

<b>Notice of Allowability</b>	Application No.	Applicant(s)
	09/683,857	CHEN ET AL.
	Examiner	Art Unit
	David L. Hogans	2813

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address--

All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. **THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS.** This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.

1.  This communication is responsive to the Amendment filed on September 15, 2004.
2.  The allowed claim(s) is/are 1-16.
3.  The drawings filed on 22 February 2002 are accepted by the Examiner.
4.  Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
  - a)  All
  - b)  Some\*
  - c)  None
 of the:
  1.  Certified copies of the priority documents have been received.
  2.  Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.
  3.  Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)).

\* Certified copies not received: \_\_\_\_\_.

Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application.  
**THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.**

5.  A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.
6.  CORRECTED DRAWINGS ( as "replacement sheets") must be submitted.
  - (a)  including changes required by the Notice of Draftsperson's Patent Drawing Review ( PTO-948) attached
    - 1)  hereto or 2)  to Paper No./Mail Date \_\_\_\_\_.
  - (b)  including changes required by the attached Examiner's Amendment / Comment or in the Office action of
 Paper No./Mail Date \_\_\_\_\_.

**Identifying Indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the header according to 37 CFR 1.121(d).**

7.  DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.

#### Attachment(s)

1.  Notice of References Cited (PTO-892)
2.  Notice of Draftsperson's Patent Drawing Review (PTO-948)
3.  Information Disclosure Statements (PTO-1449 or PTO/SB/08),  
Paper No./Mail Date \_\_\_\_\_
4.  Examiner's Comment Regarding Requirement for Deposit  
of Biological Material
5.  Notice of Informal Patent Application (PTO-152)
6.  Interview Summary (PTO-413),  
Paper No./Mail Date \_\_\_\_\_.
7.  Examiner's Amendment/Comment
8.  Examiner's Statement of Reasons for Allowance
9.  Other \_\_\_\_\_.

## **DETAILED ACTION**

This Office Action is in response to the Amendment filed on September 15, 2004.

### **EXAMINER'S AMENDMENT**

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Kilton L. Kime on October 29, 2004.

The application has been amended as follows:

- Please delete line 7 of Claim 1 and replace with: "forming a high voltage well by ion implantation of a first circuit device in the first portion of"

### ***Status of Claims***

Claims 1-16 are pending. Claims 17-46 are cancelled.

### ***Allowable Subject Matter***

2. Claims 1-16 are allowed.
3. The following is an examiner's statement of reasons for allowance.

The prior art of record fails to teach or suggest, in combination with the other claimed elements, forming a high voltage well by ion implantation of a first circuit device in the first portion of the substrate using the partially removed first ion implantation

protective layer and ion implanting a first low voltage well of a second circuit device in the second portion of the substrate using the partially removed first ion implantation protective layer and the second ion implantation protective layer.

Additionally, Applicant's arguments presented in the communication of September 15, 2004, concerning 6,258,701 to Depetro et al. have been considered and are found persuasive because Applicant's Claim 1 claims, *inter alia*, a first low voltage well of a second circuit device that is ion implanted in the second portion of the substrate using the partially removed first ion implantation protective layer and the second ion implantation protective layer.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

### **Conclusion**

4. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

6,713,347 to Cappelletti et al. fails to teach forming a high voltage well by ion implantation of a first circuit device in the first portion of the substrate using the partially removed first ion implantation protective layer.

6,207,510 to Abeln et al. fails to teach ion implanting a first low voltage well of a second circuit device in the second portion of the substrate using the partially removed first ion implantation protective layer and the second ion implantation protective layer.

5,933,731 to Tanimoto et al. fails to teach ion implanting a first low voltage well of a second circuit device in the second portion of the substrate using the partially removed first ion implantation protective layer and the second ion implantation protective layer.

6,090,652 to Kim fails to teach ion implanting a first low voltage well of a second circuit device in the second portion of the substrate using the partially removed first ion implantation protective layer and the second ion implantation protective layer.

JP09-064193 to Watanabe fails to teach ion implanting a first low voltage well of a second circuit device in the second portion of the substrate using the partially removed first ion implantation protective layer and the second ion implantation protective layer.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to David L. Hogans whose telephone number is (571) 272-1691. The examiner can normally be reached on M-F (7:30-4:30).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead Jr. can be reached on (571) 272-1702. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

DH

*Carl Whitehead*  
CARL WHITEHEAD, JR.  
SUPERVISORY PATENT EXAMINER  
TECHNOLOGY CENTER 2800